



Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	270
Number of Gates	600000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pe600-fg484

1 – ProASIC3E Device Family Overview

General Description

ProASIC3E, the third-generation family of Microsemi flash FPGAs, offers performance, density, and features beyond those of the ProASIC^{PLUS}® family. Nonvolatile flash technology gives ProASIC3E devices the advantage of being a secure, low power, single-chip solution that is Instant On. ProASIC3E is reprogrammable and offers time-to-market benefits at an ASIC-level unit cost. These features enable designers to create high-density systems using existing ASIC or FPGA design flows and tools.

ProASIC3E devices offer 1 kbit of on-chip, programmable, nonvolatile FlashROM storage as well as clock conditioning circuitry based on six integrated phase-locked loops (PLLs). ProASIC3E devices have up to three million system gates, supported with up to 504 kbits of true dual-port SRAM and up to 620 user I/Os.

Several ProASIC3E devices support the Cortex-M1 soft IP cores, and the ARM-Enabled devices have Microsemi ordering numbers that begin with M1A3PE.

Flash Advantages

Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, performance, and ease of use. Unlike SRAM-based FPGAs, flash-based ProASIC3E devices allow all functionality to be Instant On; no external boot PROM is required. On-board security mechanisms prevent access to all the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system reprogramming to support future design iterations and field upgrades with confidence that valuable intellectual property (IP) cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The ProASIC3E family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the ProASIC3E family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/ communications, computing, and avionics markets.

Security

The nonvolatile, flash-based ProASIC3E devices do not require a boot PROM, so there is no vulnerable external bitstream that can be easily copied. ProASIC3E devices incorporate FlashLock, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only an FPGA with nonvolatile flash programming can offer.

ProASIC3E devices utilize a 128-bit flash-based lock and a separate AES key to provide the highest level of protection in the FPGA industry for programmed intellectual property and configuration data. In addition, all FlashROM data in ProASIC3E devices can be encrypted prior to loading, using the industry-leading AES-128 (FIPS192) bit block cipher encryption standard. The AES standard was adopted by the National Institute of Standards and Technology (NIST) in 2000 and replaces the 1977 DES standard. ProASIC3E devices have a built-in AES decryption engine and a flash-based AES key that make them the most comprehensive programmable logic device security solution available today. ProASIC3E devices with AES-based security provide a high level of protection for secure, remote field updates over public networks such as the Internet, and ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves.

Security, built into the FPGA fabric, is an inherent component of the ProASIC3E family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. The ProASIC3E family, with FlashLock and AES security, is unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry-standard security, making remote ISP possible. A ProASIC3E device provides the best available security for programmable logic designs.

Table 2-4 • Overshoot and Undershoot Limits¹

VCCI and VMV	Average VCCI–GND Overshoot or Undershoot Duration as a Percentage of Clock Cycle ²	Maximum Overshoot/Undershoot ²
2.7 V or less	10%	1.4 V
	5%	1.49 V
3 V	10%	1.1 V
	5%	1.19 V
3.3 V	10%	0.79 V
	5%	0.88 V
3.6 V	10%	0.45 V
	5%	0.54 V

Notes:

1. Based on reliability requirements at 85°C.
2. The duration is allowed at one out of six clock cycles. If the overshoot/undershoot occurs at one out of two cycles, the maximum overshoot/undershoot has to be reduced by 0.15 V.
3. This table does not provide PCI overshoot/undershoot limits.

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC[®]3E device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges. In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-1 on page 2-4](#).

There are five regions to consider during power-up.

ProASIC3E I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-1 on page 2-4](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.2 V

Ramping down: 0.5 V < trip_point_down < 1.1 V

VCC Trip Point:

Ramping up: 0.6 V < trip_point_up < 1.1 V

Ramping down: 0.5 V < trip_point_down < 1 V

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in [Table 2-11 on page 2-11](#).
- Enable rates of output buffers—guidelines are provided for typical applications in [Table 2-12 on page 2-11](#).
- Read rate and write rate to the memory—guidelines are provided for typical applications in [Table 2-12 on page 2-11](#). The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S-CELL} * PAC4) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the [ProASIC3E FPGA Fabric User's Guide](#).

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the [ProASIC3E FPGA Fabric User's Guide](#).

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-11 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

User I/O Characteristics

Timing Model

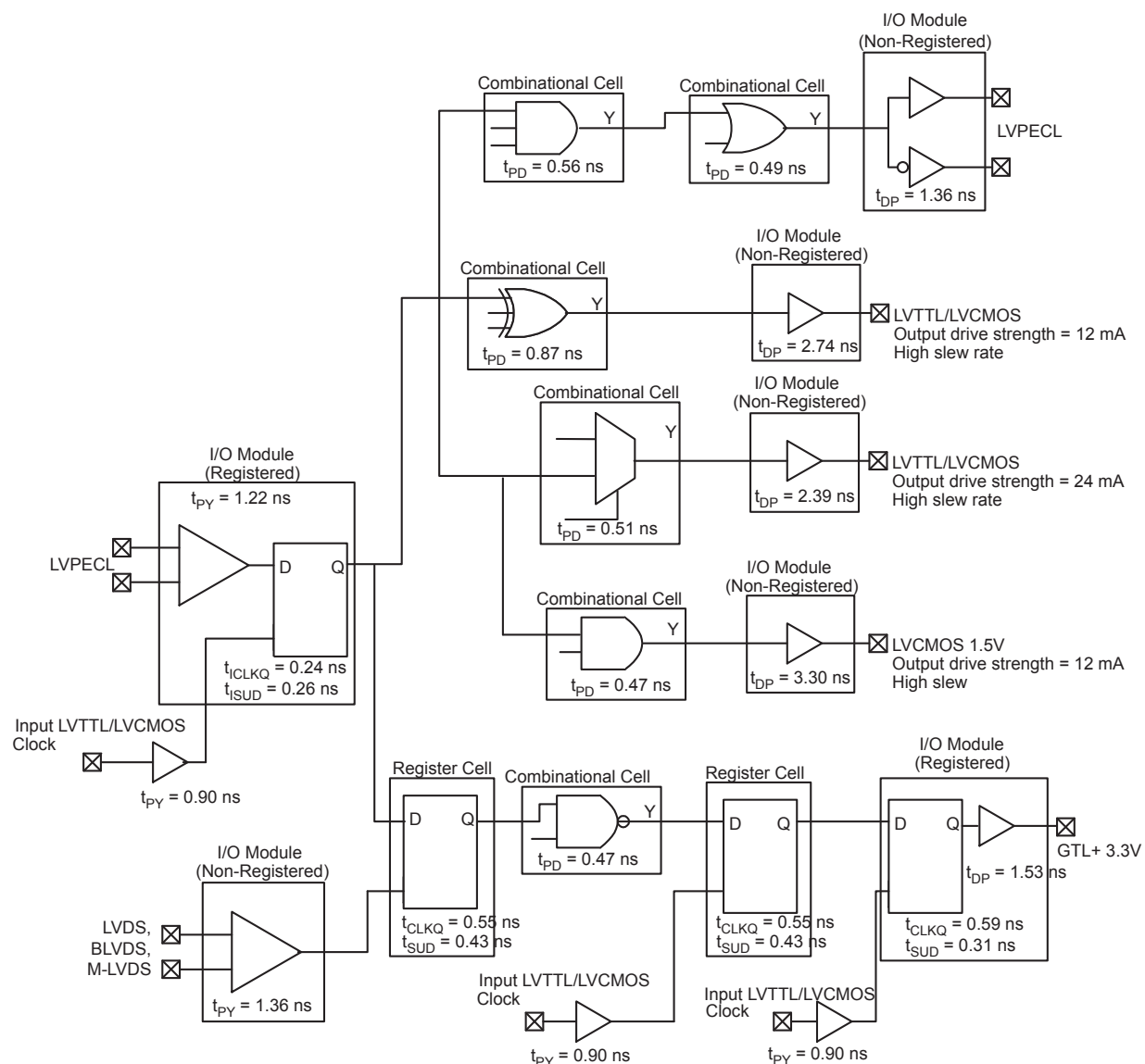


Figure 2-2 • Timing Model
Operating Conditions: -2 Speed, Commercial Temperature Range ($T_J = 70^\circ\text{C}$), Worst-Case
VCC = 1.425 V

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-41 • Minimum and Maximum DC Input and Output Levels

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	16	13	10	10
4 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4	33	25	10	10
6 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	6	6	39	32	10	10
8 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	8	8	55	66	10	10
12 mA	−0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12	55	66	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

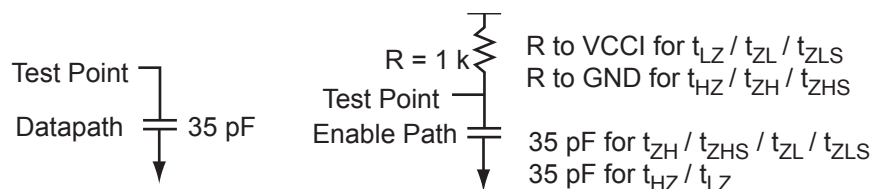


Figure 2-10 • AC Loading

Table 2-42 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	1.5	0.75	—	35

Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-45 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
Per PCI specification	Per PCI curves										10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in [Figure 2-11](#).

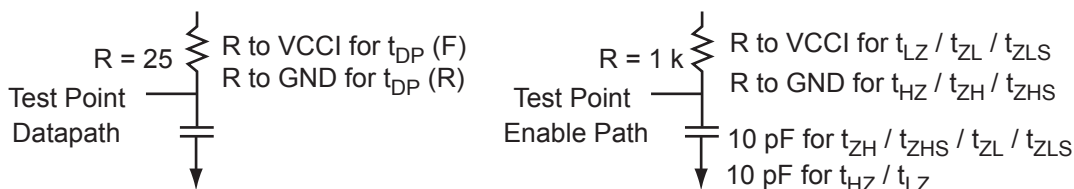


Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in [Table 2-46](#).

Table 2-46 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	3.3	0.285 * VCCI for t _{DP(R)} 0.615 * VCCI for t _{DP(F)}	—	10

Note: *Measuring point = V_{trip}. See [Table 2-15 on page 2-18](#) for a complete table of trip points.

Timing Characteristics

Table 2-47 • 3.3 V PCI/PCI-X

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.66	2.81	0.04	1.05	1.67	0.43	2.86	2.00	3.28	3.61	5.09	4.23	ns
–1	0.56	2.39	0.04	0.89	1.42	0.36	2.43	1.70	2.79	3.07	4.33	3.60	ns
–2	0.49	2.09	0.03	0.78	1.25	0.32	2.13	1.49	2.45	2.70	3.80	3.16	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

SSTL2 Class II

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). ProASIC3E devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-69 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
18 mA	−0.3	VREF − 0.2	VREF + 0.2	3.6	0.35	VCCI − 0.43	18	18	124	169	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.

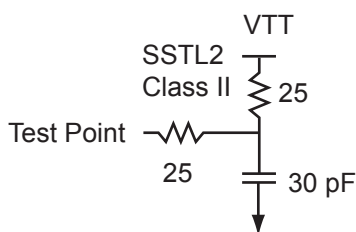


Figure 2-19 • AC Loading

Table 2-70 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF − 0.2	VREF + 0.2	1.25	1.25	1.25	30

Note: *Measuring point = V_{trip}. See Table 2-15 on page 2-18 for a complete table of trip points.

Timing Characteristics

Table 2-71 • SSTL 2 Class II

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.66	0.66	2.17	0.04	1.33	0.43	2.21	1.77			4.44	ns
−1	0.56	0.56	1.84	0.04	1.14	0.36	1.88	1.51			3.78	ns
−2	0.49	0.49	1.62	0.03	1.00	0.32	1.65	1.32			3.32	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

DDR Module Specifications

Input DDR Module

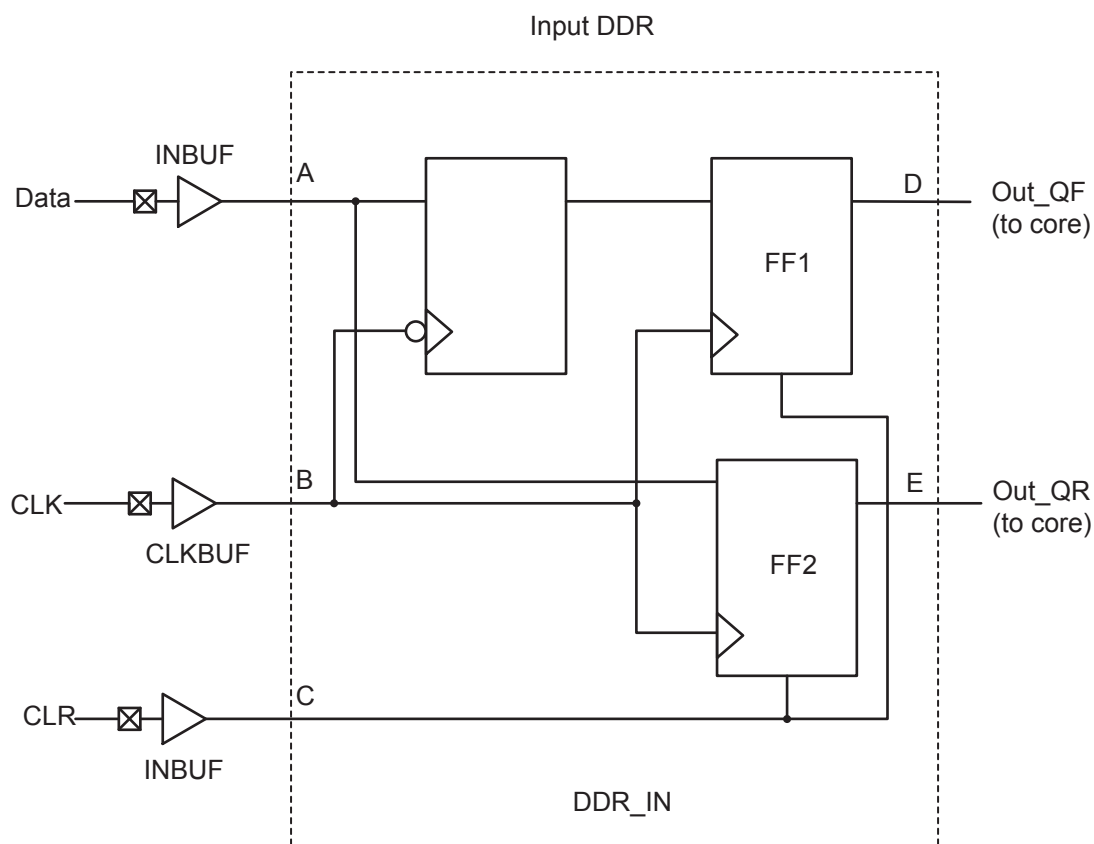


Figure 2-30 • Input DDR Timing Model

Table 2-89 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t_{DDRCLKQ1}	Clock-to-Out Out_QR	B, D
t_{DDRCLKQ2}	Clock-to-Out Out_QF	B, E
t_{DDRISUD}	Data Setup Time of DDR input	A, B
t_{DDRIHD}	Data Hold Time of DDR input	A, B
$t_{\text{DDRICLR2Q1}}$	Clear-to-Out Out_QR	C, D
$t_{\text{DDRICLR2Q2}}$	Clear-to-Out Out_QF	C, E
$t_{\text{DDRIREMCLR}}$	Clear Removal	C, B
$t_{\text{DDRIRECCLR}}$	Clear Recovery	C, B

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3E library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [Fusion](#), [IGLOO®/e](#), and [ProASIC3/E Macro Library Guide](#).

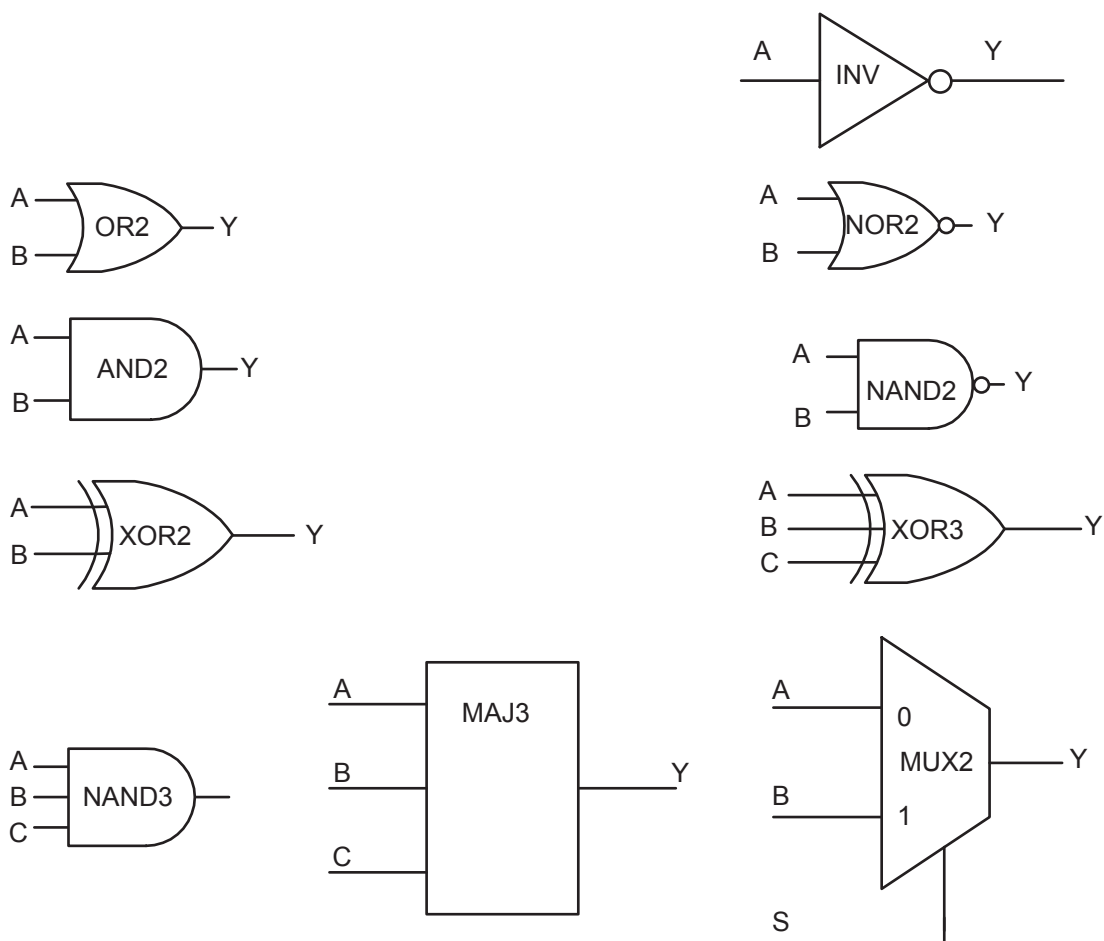


Figure 2-34 • Sample of Combinatorial Cells

Timing Characteristics

Table 2-93 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Combinatorial Cell	Equation	Parameter	-2	-1	Std.	Units
INV	$Y = !A$	t_{PD}	0.40	0.46	0.54	ns
AND2	$Y = A \cdot B$	t_{PD}	0.47	0.54	0.63	ns
NAND2	$Y = !(A \cdot B)$	t_{PD}	0.47	0.54	0.63	ns
OR2	$Y = A + B$	t_{PD}	0.49	0.55	0.65	ns
NOR2	$Y = !(A + B)$	t_{PD}	0.49	0.55	0.65	ns
XOR2	$Y = A \oplus B$	t_{PD}	0.74	0.84	0.99	ns
MAJ3	$Y = \text{MAJ}(A, B, C)$	t_{PD}	0.70	0.79	0.93	ns
XOR3	$Y = A \oplus B \oplus C$	t_{PD}	0.87	1.00	1.17	ns
MUX2	$Y = A \text{ IS } + B \text{ S}$	t_{PD}	0.51	0.58	0.68	ns
AND3	$Y = A \cdot B \cdot C$	t_{PD}	0.56	0.64	0.75	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-5](#) for derating values.

VersaTile Specifications as a Sequential Module

The ProASIC3E library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the [Fusion](#), [IGLOO/e](#), and [ProASIC3/E Macro Library Guide](#).

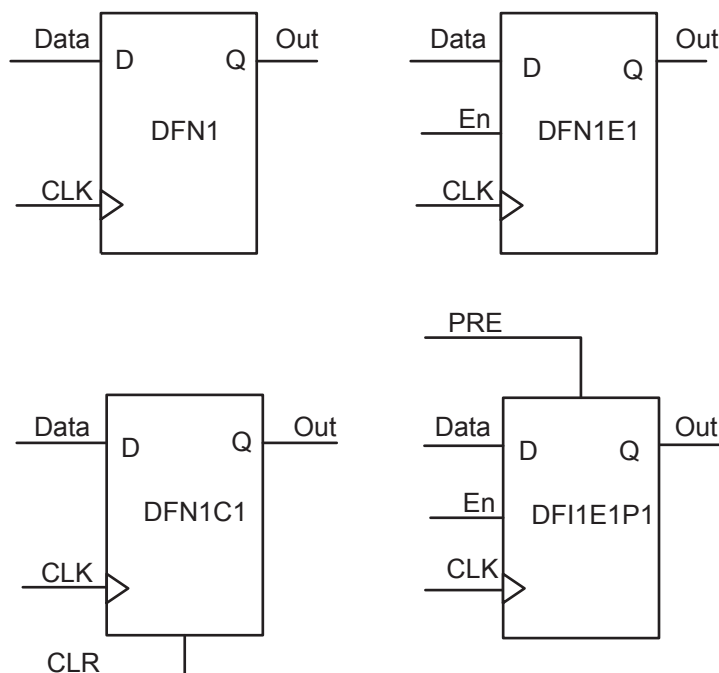


Figure 2-36 • Sample of Sequential Cells

Timing Waveforms

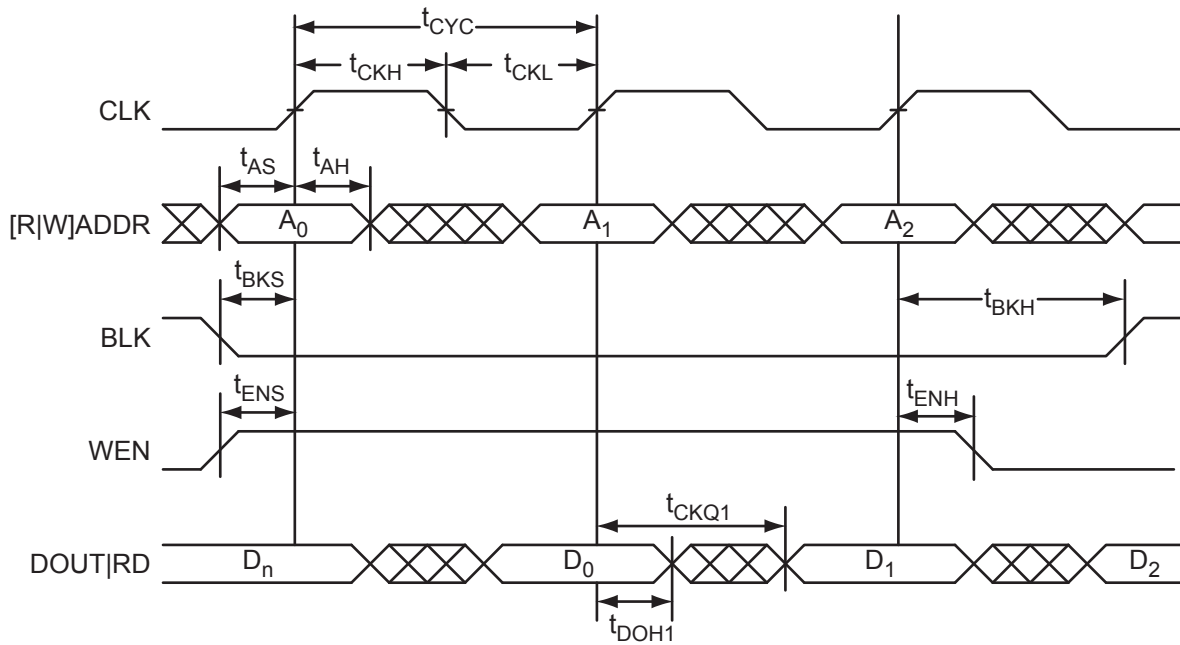


Figure 2-41 • RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.

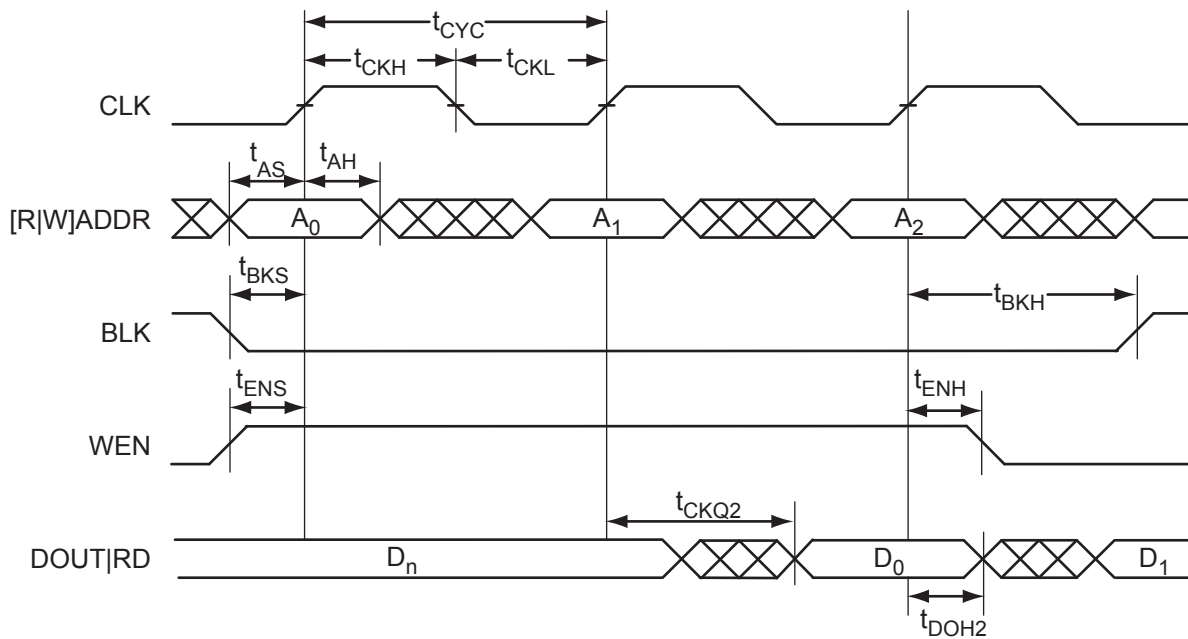


Figure 2-42 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.

3 – Pin Descriptions and Packaging

Supply Pins

GND**Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ**Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC**Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

VCCIBx**I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground through any resistor and the corresponding VCCIX grounded, then the leakage current to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it's better to float VCCIX of unused bank or tie it to GND.

VMVx**I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. x is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F**PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *ProASIC3E FPGA Fabric User's Guide* for a complete board solution for the PLL analog power supply and ground.

There are six VCCPLX pins on ProASIC3E devices.

VCOMPLA/B/C/D/E/F**PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There are six VCOMPL pins (PLL ground) on ProASIC3E devices.

PQ208	
Pin Number	A3PE1500 Function
1	GND
2	GNDQ
3	VMV7
4	GAB2/IO220PSB7V3
5	GAA2/IO221PDB7V3
6	IO221NDB7V3
7	GAC2/IO219PDB7V3
8	IO219NDB7V3
9	IO215PDB7V3
10	IO215NDB7V3
11	IO212PDB7V2
12	IO212NDB7V2
13	IO208PDB7V2
14	IO208NDB7V2
15	IO204PSB7V1
16	VCC
17	GND
18	VCCIB7
19	IO200PDB7V1
20	IO200NDB7V1
21	IO196PSB7V0
22	GFC1/IO192PSB7V0
23	GFB1/IO191PDB7V0
24	GFB0/IO191NDB7V0
25	VCOMPLF
26	GFA0/IO190NPB6V2
27	VCCPLF
28	GFA1/IO190PPB6V2
29	GND
30	GFA2/IO189PDB6V2
31	IO189NDB6V2
32	GFB2/IO188PPB6V2
33	GFC2/IO187PPB6V2
34	IO188NPB6V2
35	IO187NPB6V2
36	VCC

PQ208	
Pin Number	A3PE1500 Function
37	IO184PDB6V2
38	IO184NDB6V2
39	IO180PSB6V1
40	VCCIB6
41	GND
42	IO176PDB6V1
43	IO176NDB6V1
44	GEC1/IO169PDB6V0
45	GEC0/IO169NDB6V0
46	GEB1/IO168PPB6V0
47	GEA1/IO167PPB6V0
48	GEB0/IO168NPB6V0
49	GEA0/IO167NPB6V0
50	VMV6
51	GNDQ
52	GND
53	VMV5
54	GNDQ
55	IO166NDB5V3
56	GEA2/IO166PDB5V3
57	IO165NDB5V3
58	GEB2/IO165PDB5V3
59	IO164NDB5V3
60	GEC2/IO164PDB5V3
61	IO163PSB5V3
62	VCCIB5
63	IO161PSB5V3
64	IO157NDB5V2
65	GND
66	IO157PDB5V2
67	IO153NDB5V2
68	IO153PDB5V2
69	IO149NDB5V1
70	IO149PDB5V1
71	VCC
72	VCCIB5

PQ208	
Pin Number	A3PE1500 Function
73	IO145NDB5V1
74	IO145PDB5V1
75	IO143NDB5V1
76	IO143PDB5V1
77	IO137NDB5V0
78	IO137PDB5V0
79	IO135NDB5V0
80	IO135PDB5V0
81	GND
82	IO131NDB4V2
83	IO131PDB4V2
84	IO129NDB4V2
85	IO129PDB4V2
86	IO127NDB4V2
87	IO127PDB4V2
88	VCC
89	VCCIB4
90	IO121NDB4V1
91	IO121PDB4V1
92	IO119NDB4V1
93	IO119PDB4V1
94	IO113NDB4V0
95	GDC2/IO113PDB4V0
96	IO112NDB4V0
97	GND
98	GDB2/IO112PDB4V0
99	GDA2/IO111PSB4V0
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV4
105	GND
106	VPUMP
107	GNDQ
108	TDO

FG484	
Pin Number	A3PE600 Function
H19	IO41PDB2V0
H20	VCC
H21	NC
H22	NC
J1	IO123NDB7V0
J2	IO123PDB7V0
J3	NC
J4	IO124PDB7V0
J5	IO125PDB7V0
J6	IO126PDB7V0
J7	IO130NDB7V1
J8	VCCIB7
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB2
J16	IO38NDB2V0
J17	IO40NDB2V0
J18	IO40PDB2V0
J19	IO45PPB2V1
J20	NC
J21	IO48PDB2V1
J22	IO46PDB2V1
K1	IO121NDB7V0
K2	IO121PDB7V0
K3	NC
K4	IO124NDB7V0
K5	IO125NDB7V0
K6	IO126NDB7V0
K7	GFC1/IO120PPB7V0
K8	VCCIB7
K9	VCC
K10	GND

FG484	
Pin Number	A3PE600 Function
K11	GND
K12	GND
K13	GND
K14	VCC
K15	VCCIB2
K16	GCC1/IO50PPB2V1
K17	IO44NDB2V1
K18	IO44PDB2V1
K19	IO49NPB2V1
K20	IO45NPB2V1
K21	IO48NDB2V1
K22	IO46NDB2V1
L1	NC
L2	IO122PDB7V0
L3	IO122NDB7V0
L4	GFB0/IO119NPB7V0
L5	GFA0/IO118NDB6V1
L6	GFB1/IO119PPB7V0
L7	VCOMPLF
L8	GFC0/IO120NPB7V0
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	VCC
L15	GCC0/IO50NPB2V1
L16	GCB1/IO51PPB2V1
L17	GCA0/IO52NPB3V0
L18	VCOMPLC
L19	GCB0/IO51NPB2V1
L20	IO49PPB2V1
L21	IO47NDB2V1
L22	IO47PDB2V1
M1	NC
M2	IO114NPB6V1

FG484	
Pin Number	A3PE600 Function
M3	IO117NDB6V1
M4	GFA2/IO117PDB6V1
M5	GFA1/IO118PDB6V1
M6	VCCPLF
M7	IO116NDB6V1
M8	GFB2/IO116PDB6V1
M9	VCC
M10	GND
M11	GND
M12	GND
M13	GND
M14	VCC
M15	GCB2/IO54PPB3V0
M16	GCA1/IO52PPB3V0
M17	GCC2/IO55PPB3V0
M18	VCCPLC
M19	GCA2/IO53PDB3V0
M20	IO53NDB3V0
M21	IO56PDB3V0
M22	NC
N1	IO114PPB6V1
N2	IO111NDB6V1
N3	NC
N4	GFC2/IO115PPB6V1
N5	IO113PPB6V1
N6	IO112PDB6V1
N7	IO112NDB6V1
N8	VCCIB6
N9	VCC
N10	GND
N11	GND
N12	GND
N13	GND
N14	VCC
N15	VCCIB3
N16	IO54NPB3V0

FG484	
Pin Number	A3PE1500 Function
A1	GND
A2	GND
A3	VCCIB0
A4	IO05NDB0V0
A5	IO05PDB0V0
A6	IO11NDB0V1
A7	IO11PDB0V1
A8	IO15PDB0V1
A9	IO17PDB0V2
A10	IO27NDB0V3
A11	IO27PDB0V3
A12	IO32PDB1V0
A13	IO43PDB1V1
A14	IO47NDB1V1
A15	IO47PDB1V1
A16	IO51NDB1V2
A17	IO51PDB1V2
A18	IO54NDB1V3
A19	NC
A20	VCCIB1
A21	GND
A22	GND
AA1	GND
AA2	VCCIB6
AA3	NC
AA4	IO161PDB5V3
AA5	IO155NDB5V2
AA6	IO155PDB5V2
AA7	IO154NDB5V2
AA8	IO154PDB5V2
AA9	IO143PDB5V1
AA10	IO143NDB5V1
AA11	IO131PPB4V2
AA12	IO129NDB4V2
AA13	IO129PDB4V2
AA14	NC

FG484	
Pin Number	A3PE1500 Function
AA15	NC
AA16	IO117NDB4V0
AA17	IO117PDB4V0
AA18	IO115NDB4V0
AA19	IO115PDB4V0
AA20	NC
AA21	VCCIB3
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB5
AB4	IO159NDB5V3
AB5	IO159PDB5V3
AB6	IO149NDB5V1
AB7	IO149PDB5V1
AB8	IO138NDB5V0
AB9	IO138PDB5V0
AB10	NC
AB11	NC
AB12	IO127NDB4V2
AB13	IO127PDB4V2
AB14	IO125NDB4V1
AB15	IO125PDB4V1
AB16	IO122NDB4V1
AB17	IO122PDB4V1
AB18	NC
AB19	NC
AB20	VCCIB4
AB21	GND
AB22	GND
B1	GND
B2	VCCIB7
B3	NC
B4	IO03NDB0V0
B5	IO03PDB0V0
B6	IO10NDB0V1

FG484	
Pin Number	A3PE1500 Function
B7	IO10PDB0V1
B8	IO15NDB0V1
B9	IO17NDB0V2
B10	IO20PDB0V2
B11	IO29PDB0V3
B12	IO32NDB1V0
B13	IO43NDB1V1
B14	NC
B15	NC
B16	IO53NDB1V2
B17	IO53PDB1V2
B18	IO54PDB1V3
B19	NC
B20	NC
B21	VCCIB2
B22	GND
C1	VCCIB7
C2	NC
C3	NC
C4	NC
C5	GND
C6	IO07NDB0V0
C7	IO07PDB0V0
C8	VCC
C9	VCC
C10	IO20NDB0V2
C11	IO29NDB0V3
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	A3PE1500 Function
V15	IO112NDB4V0
V16	GDB2/IO112PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO105NDB3V2
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO165NDB5V3
W6	GEB2/IO165PDB5V3
W7	IO164NDB5V3
W8	IO153NDB5V2
W9	IO153PDB5V2
W10	IO147NDB5V1
W11	IO133NDB4V2
W12	IO130NDB4V2
W13	IO130PDB4V2
W14	IO113NDB4V0
W15	GDC2/IO113PDB4V0
W16	IO111NDB4V0
W17	GDA2/IO111PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO161NDB5V3
Y5	GND
Y6	IO163NDB5V3

FG484	
Pin Number	A3PE1500 Function
Y7	IO163PDB5V3
Y8	VCC
Y9	VCC
Y10	IO147PDB5V1
Y11	IO133PDB4V2
Y12	IO131NPB4V2
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-19 • I/O Output Buffer Maximum Resistances¹ and Table 2-21 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33853). 3.3 V LVCMOS Wide Range information was separated from regular 3.3 V LVCMOS and placed into its own new section, " 3.3 V LVCMOS Wide Range ". Values of IOSH and IOSL were added in Table 2-29 • Minimum and Maximum DC Input and Output Levels (SAR 33853).	2-20, 2-27
	The formulas in the table notes for Table 2-20 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 34755).	2-21
	The AC Loading figures in the " Single-Ended I/O Characteristics " section were updated to match tables in the " Summary of I/O Timing Characteristics – Default I/O Software Settings " section (SAR 34889).	2-24
	The titles and subtitles for Table 2-31 • 3.3 V LVCMOS Wide Range High Slew and Table 2-32 • 3.3 V LVCMOS Wide Range Low Slew were corrected (SAR 37227).	2-28, 2-29
	The following notes were removed from Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 34812): ±5% Differential input voltage = ±350 mV	2-50
	Minimum pulse width High and Low values were added to the tables in the " Global Tree Timing Characteristics " section. The maximum frequency for global clock parameter was removed from these tables because a frequency on the global is only an indication of what the global network can do. There are other limiters such as the SRAM, I/Os, and PLL. SmartTime software should be used to determine the design frequency (SAR 36957).	2-68
	A note was added to Table 2-98 • ProASIC3E CCC/PLL Specification indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34824).	2-70
	The following figures were deleted. Reference was made to a new application note, Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs , which covers these cases in detail (SAR 34872). Figure 2-44 • Write Access after Write onto Same Address Figure 2-45 • Read Access after Write onto Same Address Figure 2-46 • Write Access after Read onto Same Address The port names in the SRAM " Timing Waveforms ", SRAM " Timing Characteristics " tables, Figure 2-49 • FIFO Reset , and the FIFO " Timing Characteristics " tables were revised to ensure consistency with the software names (SAR 35750).	2-74, 2-75, 2-79, 2-82
	The " Pin Descriptions and Packaging " chapter is new (SAR 34771).	3-1
July 2010	Package names used in the " Package Pin Assignments " section were revised to match standards given in Package Mechanical Drawings (SAR 34771).	4-1
	Pin E6 for the FG256 package was corrected from VvB0 to VCCIB0 (SARs 30364, 31597, 26243).	4-9
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The " ProASIC3E Device Status " table on page II indicates the status for each device in the device family.	N/A

Revision	Changes	Page														
Revision 9 (Aug 2009) Product Brief v1.2	All references to speed grade –F have been removed from this document.	N/A														
DC and Switching Characteristics v1.3	The "Pro I/Os with Advanced I/O Standards" section was revised to add definitions of hot-swap and cold-sparing.	1-6														
	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A														
	IIL and IIH input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A														
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A														
	In the Table 2-2 • Recommended Operating Conditions ¹ "3.0 V DC supply voltage" and note 4 are new.	2-2														
	The Table 2-4 • Overshoot and Undershoot Limits ¹ table was updated.	2-3														
	The Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays table was updated.	2-5														
	There are new parameters and data was updated in the Table 2-99 • RAM4K9 table.	2-76														
	There are new parameters and data was updated in the Table 2-100 • RAM512X18 table.	2-77														
Revision 8 (Feb 2008) Product Brief v1.1	Table 1-2 • ProASIC3E FPGAs Package Sizes Dimensions is new.	1-II														
Revision 7 (Jun 2008) DC and Switching Characteristics v1.2	The title of Table 2-4 • Overshoot and Undershoot Limits ¹ was modified to remove "as measured on quiet I/Os." Table note 2 was revised to remove "estimated SSO density over cycles." Table note 3 was deleted.	2-3														
	Table 2-78 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-50														
Revision 6 (Jun 2008)	The A3PE600 "FG484" table was missing G22. The pin and its function were added to the table.	4-27														
Revision 5 (Jun 2008) Packaging v1.4	The naming conventions changed for the following pins in the "FG484" for the A3PE600: <table><tr><th>Pin Number</th><th>New Function Name</th></tr><tr><td>J19</td><td>IO45PPB2V1</td></tr><tr><td>K20</td><td>IO45NPB2V1</td></tr><tr><td>M2</td><td>IO114NPB6V1</td></tr><tr><td>N1</td><td>IO114PPB6V1</td></tr><tr><td>N4</td><td>GFC2/IO115PPB6V1</td></tr><tr><td>P3</td><td>IO115NPB6V1</td></tr></table>	Pin Number	New Function Name	J19	IO45PPB2V1	K20	IO45NPB2V1	M2	IO114NPB6V1	N1	IO114PPB6V1	N4	GFC2/IO115PPB6V1	P3	IO115NPB6V1	4-22
Pin Number	New Function Name															
J19	IO45PPB2V1															
K20	IO45NPB2V1															
M2	IO114NPB6V1															
N1	IO114PPB6V1															
N4	GFC2/IO115PPB6V1															
P3	IO115NPB6V1															
Revision 4 (Apr 2008) Product Brief v1.0	The product brief portion of the datasheet was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A														
Packaging v1.3	The "FG324" package diagram was replaced.	4-12														

Revision	Changes	Page
v2.1 (continued)	The words "ambient temperature" were added to the temperature range in the "Temperature Grade Offerings", "Speed Grade and Temperature Grade Matrix", and "Speed Grade and Temperature Grade Matrix" sections.	1-I
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	1-I
	The caption "Main (chip)" in Figure 2-9 • Overview of Automotive ProASIC3 VersaNet Global Network was changed to "Chip (main)."	2-9
	The T_J parameter in Table 3-2 • Recommended Operating Conditions was changed to T_A , ambient temperature, and table notes 4–6 were added.	3-2
	The "PLL Macro" section was updated to add information on the VCO and PLL outputs during power-up.	2-15
v2.0 (April 2007)	In the "Temperature Grade Offerings" section, Ambient was deleted.	iii
	Ambient was deleted from "Temperature Grade Offerings".	iii
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	The "PLL Macro" section was updated to include power-up information.	2-15
	Table 2-13 • ProASIC3E CCC/PLL Specification was updated.	2-30
	Figure 2-19 • Peak-to-Peak Jitter Definition is new.	2-18
	The "SRAM and FIFO" section was updated with operation and timing requirement information.	2-21
	The "RESET" section was updated with read and write information.	2-25
	The "RESET" section was updated with read and write information.	2-25
	The "Introduction" in the "Advanced I/Os" section was updated to include information on input and output buffers being disabled.	2-28
	In the Table 2-15 • Levels of Hot-Swap Support, the ProASIC3 compliance descriptions were updated for levels 3 and 4.	2-34
	Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Notes 3, 4, and 5 were added to Table 2-17 • Comparison Table for 5 V–Compliant Receiver Scheme. 5 x 52.72 was changed to 52.7 and the Maximum current was updated from 4 x 52.7 to 5 x 52.7.	2-40
	The "VCCPLF PLL Supply Voltage" section was updated.	2-50
	The "VPUMP Programming Supply Voltage" section was updated.	2-50
	The "GL Globals" section was updated to include information about direct input into quadrant clocks.	2-51
	VJTAG was deleted from the "TCK Test Clock" section.	2-51
	In Table 2-22 • Recommended Tie-Off Values for the TCK and TRST Pins, TSK was changed to TCK in note 2. Note 3 was also updated.	2-51
	Ambient was deleted from Table 3-2 • Recommended Operating Conditions. VPUMP programming mode was changed from "3.0 to 3.6" to "3.15 to 3.45".	3-2
	Note 3 is new in Table 3-4 • Overshoot and Undershoot Limits (as measured on quiet I/Os).	3-2
	In EQ 3-2, 150 was changed to 110 and the result changed to 5.88.	3-5

Revision	Changes	Page
Advance v0.3 (continued)	The "Methodology" section was updated.	3-9
	The A3PE3000 "208-Pin PQFP" pin table was updated.	4-6